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(71) Applicants: ADVANCED MICRO DEVICES, INC. [US/US]; One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US). FUJITSU LIMITED [JP/JP]; 1-1, Kamikodanaka 4-chome, Nakahara-ku, Kawasaki-shi, Kanagawa 211 (JP).

(72) Inventors: HUI, Angela, T.; 362 Pilgrim Loop, Fremont, CA 94539 (US). OGURA, Jusuke; 10183 Denison Avenue, Cupertino, CA 95014 (US).

(74) Agent: RODDY, Richard, J.; Advanced Micro Devices, Inc., One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

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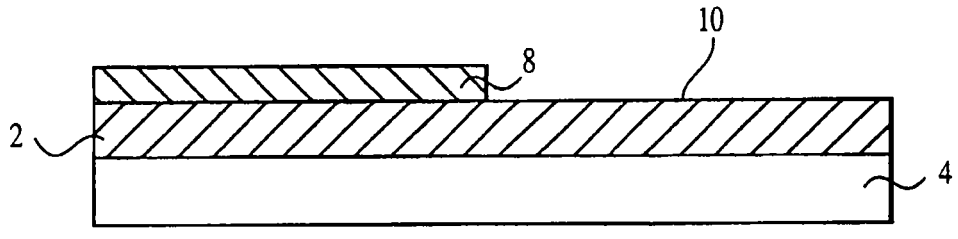


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ACTION

(54) Title: METHOD FOR FORMING HIGH QUALITY MULTIPLE THICKNESS OXIDE LAYERS BY USING HIGH TEMPERATURE DESCUM



(57) Abstract: A method for forming high quality multiple thickness oxide layers having different thicknesses by eliminating descum induced defects. The method includes forming an oxide layer (2), masking the oxide layer with a photoresist layer (8), and developing the photoresist layer to expose at least one region (10) of the oxide layer. The substrate is then heated and descummed to remove any residue resulting from developing the photoresist. Alternatively, the photoresist layer (8) may be cured prior to heating and descumming the substrate. The oxide layer (2) is then etched, and the remaining photoresist (8) is stripped before another layer of oxide (14) is grown on the substrate.

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